ERRATA

Erratum: Radiation emitted by quantum-well InGaAs structures

I. Spontaneous emission spectra [Semiconductors 32, 423–427 (April 1998)]

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The correct figures for this article should read as follows:

FIG. 1. Relative spectral density P of the radiation of an InGaAs quantum well at 286 K. Pump current I , mA: 1 — 1, 2 — 2, 3 — 5, 4 — 10, 5 — 50, 6 — 100, 7 — 150, 8 — 200. The spectra 3 and 4 were obtained in the direct-current regime.

FIG. 2. Relative spectral density P of the radiation of an InGaAs quantum well at 4.2 K. Pump current I , mA: 1 — 1, 2 — 2, 3 — 10, 4 — 20, 5 — 100, 6 — 150, 7 — 200. The spectra 1 and 4 were obtained in the direct current regime.